Figure 1. PL image of as-grown defects in CZ Si

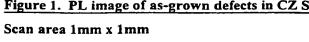
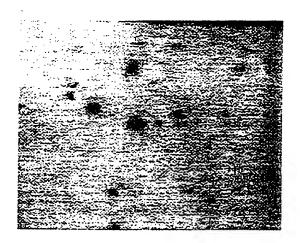
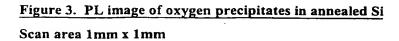


Figure 2. PL image of as-grown defects in CZ Si after Fe contamination 1x 10 atoms.cm Scan area 1mm x 1mm





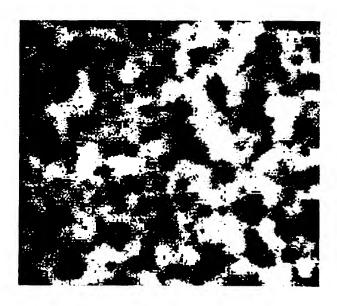
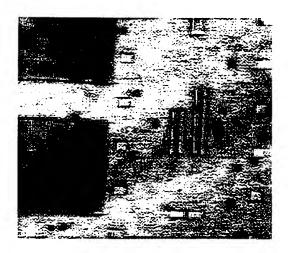


Figure 4. PL image of Ni silicide precipitates in CMOS processed test wafer Scan area 500 x 500 μm



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Figure 5. PL image of Cu silicide precipitates in CMOS processed test wafer Scan area $100 \times 100 \ \mu m$

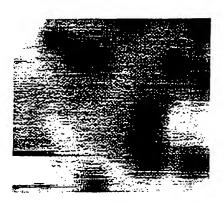
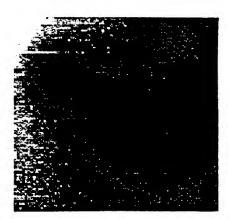


Figure 6. PL image of Cu silicide precipitates in CMOS processed test wafer, a) high injection, b) low injection.

Scan area 37 x 39 µm

a)

b)



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Figure 7. Micrograph of LOCOS test structure

Scan area 120 x 60 μm

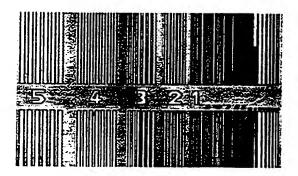


Figure 8. PL image of LOCOS test structure revealing a high density of dislocations

Scan area 120 x 60 μm

